Rev. 1 — 17 August 2010

Product data sheet

1. Product profile

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

1.2 Features and benefits

- Internally matched to 50 Ω
- A gain of 22.2 dB at 250 MHz increasing to 23.0 dB at 2150 MHz
- Output power at 1 dB gain compression = 2 dBm
- Supply current = 14.3 mA at a supply voltage of 3.3 V
- Reverse isolation > 29 dB up to 2 GHz
- Good linearity with low second order and third order products
- Noise figure = 4 dB at 950 MHz

1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

2. Pinning information

Table 1. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|------|-------------|--------------------|----------------|
| 1 | V_{CC} | | |
| 2, 5 | GND2 | | \sim |
| 3 | RF_OUT | | 6— |
| 4 | GND1 | 0 | 4 2,5 |
| 6 | RF_IN | <u> </u> 1 | sym052 |

3. Ordering information

Table 2. Ordering information

| Type number | Package | | | | | |
|-------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| BGA2801 | - | plastic surface-mounted package; 6 leads | SOT363 | | | |



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MMIC wideband amplifier

4. Marking

Table 3. Marking

| | <u> </u> | |
|-------------|---------------------------|---------------------------|
| Type number | Marking code | Description |
| BGA2801 | * = - : made in Hong Kong | |
| | | * = p : made in Hong Kong |
| | | * = W : made in China |
| | | * = t : made in Malaysia |

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|-------------------------|-------------------------|-----|-------|------|
| V_{CC} | supply voltage | RF input AC coupled | 3.0 | 3.6 | V |
| I _{CC} | supply current | | - | 55 | mΑ |
| P _{tot} | total power dissipation | T _{sp} = 90 °C | - | 200 | mW |
| T _{stg} | storage temperature | | -40 | +125 | °C |
| Tj | junction temperature | | - | 125 | °C |
| P _{drive} | drive power | | - | -16.5 | dBm |

6. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Тур | Unit |
|----------------|--|--|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | $P_{tot} = 200 \text{ mW}; T_{sp} = 90 ^{\circ}\text{C}$ | 300 | K/W |

7. Characteristics

Table 6. Characteristics

 $V_{CC} = 3.3 \text{ V; } Z_S = Z_L = 50 \Omega; P_i = -30 \text{ dBm; } T_{amb} = 25 \text{ °C; measured on demo board; unless otherwise specified.}$

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|--------------------|--|------|-----------|------------------|----------------|
| V_{CC} | supply voltage | | 3.0 | 3.3 | 3.6 | V |
| I _{CC} | supply current | | 12.2 | 14.3 | 16.3 | mΑ |
| Gp | power gain | f = 250 MHz | 21.6 | 22.2 | 22.8 | dB |
| | | f = 950 MHz | 21.7 | 22.4 | 23.1 | dB |
| | | f = 2150 MHz | 21.5 | 23.0 | 24.4 | dB |
| RL_{in} | input return loss | f = 250 MHz | 15 | 17 | 19 | dB |
| | | f = 950 MHz | 15 | 17 | 19 | dB |
| | | f = 2150 MHz | 10 | 12 | 19 | dB |
| RL_{out} | output return loss | f = 250 MHz | 13 | 17 | 22 | dB |
| | | f = 950 MHz | 14 | 15 | 16 | dB |
| | | f = 2150 MHz | 10 | 12 | 15 | dB |
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MMIC wideband amplifier

Table 6. Characteristics ...continued

 $V_{CC} = 3.3 \text{ V}; Z_S = Z_L = 50 \Omega; P_i = -30 \text{ dBm}; T_{amb} = 25 \text{ °C}; \text{ measured on demo board; unless otherwise specified.}$

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|---------------------------------------|---|------------|-----|-----|------|
| ISL | isolation | f = 250 MHz | 58 | 78 | 99 | dB |
| | | f = 950 MHz | 46 | 47 | 49 | dB |
| | | f = 2150 MHz | 29 | 32 | 34 | dB |
| NF | noise figure | f = 250 MHz | 3.4 | 3.8 | 4.3 | dB |
| | | f = 950 MHz | 3.4 | 3.8 | 4.3 | dB |
| | | f = 2150 MHz | 3.5 | 3.9 | 4.4 | dB |
| B _{-3dB} | -3 dB bandwidth | 3 dB below gain at 1 GHz | 2.5 | 2.8 | 3.1 | GHz |
| K | Rollett stability factor | f = 250 MHz | 252 | 308 | 363 | |
| | | f = 950 MHz | 7 | 8 | 10 | |
| | | f = 2150 MHz | 0.7 | 1.3 | 1.9 | |
| P _{L(sat)} | saturated output power | f = 250 MHz | 4 | 4 | 5 | dBm |
| | | f = 950 MHz | 2 | 4 | 5 | dBm |
| | | f = 2150 MHz | 1 | 2 | 3 | dBm |
| P _{L(1dB)} | output power at 1 dB gain compression | f = 250 MHz | 1 | 2 | 3 | dBm |
| | | f = 950 MHz | 0 | 2 | 3 | dBm |
| | | f = 2150 MHz | -1 | 0 | 1 | dBm |
| IP3 _I | input third-order intercept point | P _{drive} = -34 dBm (for each tone) | | | | |
| | | $f_1 = 250 \text{ MHz}; f_2 = 251 \text{ MHz}$ | -10 | -8 | -6 | dBm |
| | | f ₁ = 950 MHz; f ₂ = 951 MHz | -11 | -8 | -6 | dBm |
| | | f ₁ = 2150 MHz; f ₂ = 2151 MHz | -17 | -14 | -10 | dBm |
| IP3 _O | output third-order intercept point | P _{drive} = -34 dBm (for each tone) | | | | |
| | | f ₁ = 250 MHz; f ₂ = 251 MHz | 12 | 14 | 16 | dBm |
| | | f ₁ = 950 MHz; f ₂ = 951 MHz | 12 | 14 | 16 | dBm |
| | | f ₁ = 2150 MHz; f ₂ = 2151 MHz | 6 | 9 | 13 | dBm |
| P _{L(2H)} | second harmonic output power | P _{drive} = −31 dBm | | | | |
| | | $f_{1H} = 250 \text{ MHz}; f_{2H} = 500 \text{ MHz}$ | -62 | -60 | -58 | dBm |
| | | $f_{1H} = 950 \text{ MHz}; f_{2H} = 1900 \text{ MHz}$ | –51 | -50 | -48 | dBm |
| ΔΙΜ2 | second-order intermodulation distance | $P_{drive} = -34 \text{ dBm (for each tone)}$ | | | | |
| | | f ₁ = 250 MHz; f ₂ = 251 MHz | 34 | 45 | 56 | dBc |
| | | $f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$ | 27 | 39 | 50 | dBc |
| | | | | | | |

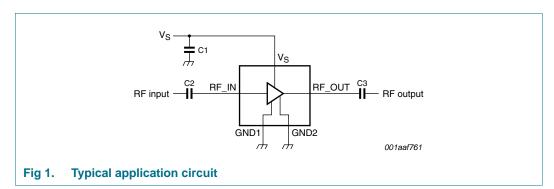
8. Application information

<u>Figure 1</u> shows a typical application circuit for the BGA2801 MMIC. The device is internally matched to $50~\Omega$, and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

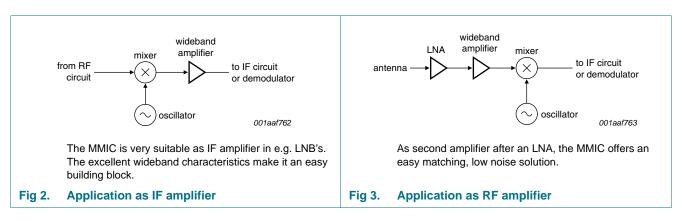
The 22 nF supply decoupling capacitor C1 should be located as close as possible to the MMIC.

BGA2801

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.



8.1 Application examples



8.2 Graphs

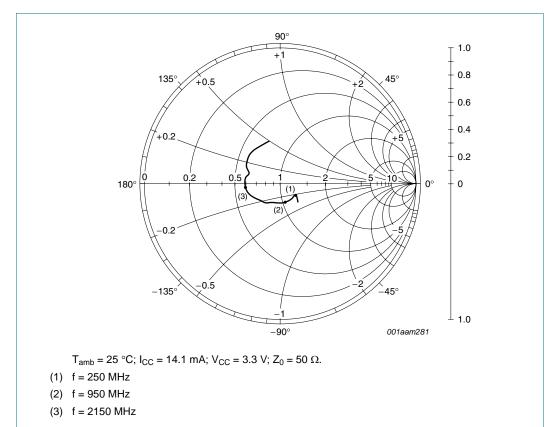
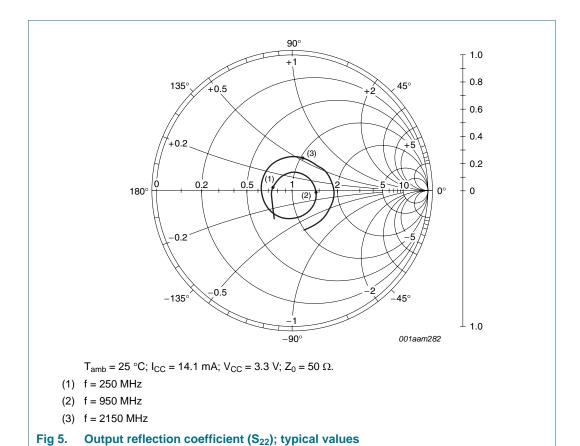
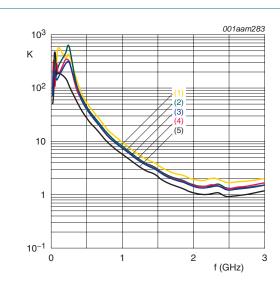


Fig 4. Input reflection coefficient (S₁₁); typical values

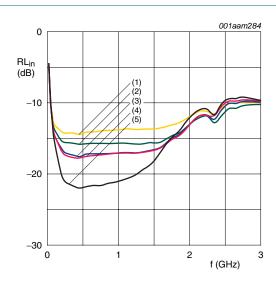




 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

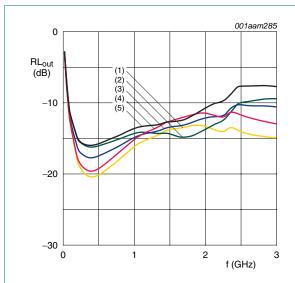
Fig 6. Rollett stability factor as function of frequency; typical values



 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

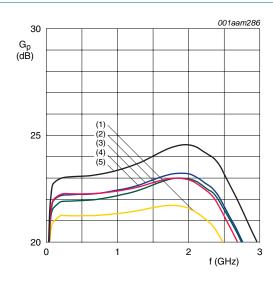
Fig 7. Input return loss as function of frequency; typical values



 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

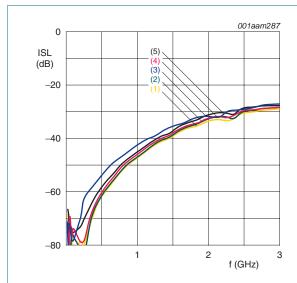
Fig 8. Output return loss as function of frequency; typical values



 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

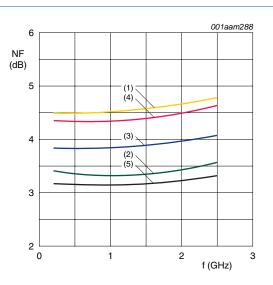
Fig 9. Insertion power gain as function of frequency; typical values



 $P_{drive} = -40 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

Fig 10. Isolation as function of frequency; typical values



 $Z_0 = 50 \Omega$.

- (1) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 12.52 \,\text{mA}$
- (2) $V_{CC} = 3.0 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 12.67 \,\text{mA}$
- (3) $V_{CC} = 3.3 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; $I_{CC} = 14.08 \,\text{mA}$
- (4) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = 85 \,^{\circ}\text{C}$; $I_{CC} = 15.30 \,\text{mA}$
- (5) $V_{CC} = 3.6 \text{ V}$; $T_{amb} = -40 \,^{\circ}\text{C}$; $I_{CC} = 16.51 \,\text{mA}$

Fig 11. Noise figure as function of frequency; typical values

8.3 Tables

Table 7. Supply current over temperature and supply voltages Typical values.

| Symbol | Parameter | Conditions | T _{amb} (°C) | | | Unit |
|---------------------|----------------|--------------------------|-----------------------|-------|-------|------|
| | | | -40 | 25 | 85 | |
| I _{CC} sup | supply current | $V_{CC} = 3.0 \text{ V}$ | 12.67 | 12.24 | 12.52 | mΑ |
| | | $V_{CC} = 3.3 \text{ V}$ | 14.85 | 14.08 | 14.27 | mΑ |
| | | $V_{CC} = 3.6 \text{ V}$ | 16.51 | 15.65 | 15.30 | mΑ |

Table 8. Second harmonic output power over temperature and supply voltages *Typical values*.

| Symbol | Parameter | Conditions | Tamb | (°C) | | Unit |
|-------------|------------------------------|--|------------|------|-----|------|
| | | | -40 | 25 | 85 | |
| $P_{L(2H)}$ | second harmonic output power | $f = 250 \text{ MHz}; P_{drive} = -33 \text{ dBm}$ | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | -53 | -58 | -59 | dBm |
| | | $V_{CC} = 3.3 \text{ V}$ | -56 | -60 | -59 | dBm |
| | | $V_{CC} = 3.6 \text{ V}$ | -58 | -60 | -59 | dBm |
| | | $f = 950 \text{ MHz}; P_{drive} = -33 \text{ dBm}$ | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | -46 | -50 | -54 | dBm |
| | | $V_{CC} = 3.3 \text{ V}$ | -47 | -50 | -53 | dBm |
| | | $V_{CC} = 3.6 \text{ V}$ | -47 | -49 | -52 | dBm |

BGA2801

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Table 9. Input power at 1 dB gain compression over temperature and supply voltages *Typical values*.

| Symbol | Parameter | Conditions | T _{amb} (°C) | | | Unit |
|--------------|--------------------------------------|--------------------------|-----------------------|-----|-----|------|
| | | | -40 | 25 | 85 | |
| $P_{i(1dB)}$ | input power at 1 dB gain compression | f = 250 MHz | , | | ' | |
| | | $V_{CC} = 3.0 \text{ V}$ | -20 | -20 | -20 | dBm |
| | $V_{CC} = 3.3 \text{ V}$ | -20 | -19 | -19 | dBm | |
| | $V_{CC} = 3.6 \text{ V}$ | -19 | -19 | -19 | dBm | |
| | f = 950 MHz | | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | -20 | -20 | -20 | dBm |
| | | $V_{CC} = 3.3 \text{ V}$ | -20 | -20 | -20 | dBm |
| | | $V_{CC} = 3.6 \text{ V}$ | -19 | -19 | -19 | dBm |
| | | f = 2150 MHz | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | -22 | -22 | -22 | dBm |
| | | $V_{CC} = 3.3 \text{ V}$ | -21 | -21 | -22 | dBm |
| | | $V_{CC} = 3.6 \text{ V}$ | -21 | -21 | -22 | dBm |

Table 10. Output power at 1 dB gain compression over temperature and supply voltages *Typical values*.

| Symbol | Parameter | Conditions | T _{amb} (°C) | | | Unit |
|--------------|---------------------------------------|--------------------------|-----------------------|----|-----|------|
| | | | -40 | 25 | 85 | |
| $P_{L(1dB)}$ | output power at 1 dB gain compression | f = 250 MHz | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 1 | 1 | 0 | dBm |
| | $V_{CC} = 3.3 \text{ V}$ | 2 | 2 | 1 | dBm | |
| | $V_{CC} = 3.6 \text{ V}$ | 3 | 3 | 2 | dBm | |
| | f = 950 MHz | | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 1 | 0 | 0 | dBm |
| | | $V_{CC} = 3.3 \text{ V}$ | 2 | 2 | 1 | dBm |
| | | $V_{CC} = 3.6 \text{ V}$ | 3 | 3 | 2 | dBm |
| | | f = 2150 MHz | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 0 | -1 | -2 | dBm |
| | | $V_{CC} = 3.3 \text{ V}$ | 1 | 0 | -1 | dBm |
| | | $V_{CC} = 3.6 \text{ V}$ | 2 | 1 | 0 | dBm |

Table 11. Saturated output power over temperature and supply voltages *Typical values.*

| Symbol | Parameter | Conditions | T _{amb} | T _{amb} (°C) | | | |
|--------------|------------------------|--------------------------|------------------|-----------------------|----|-----|--|
| | | | -40 | 25 | 85 | | |
| $P_{L(sat)}$ | saturated output power | f = 250 MHz | | ' | ' | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 3 | 3 | 3 | dBm | |
| | | $V_{CC} = 3.3 \text{ V}$ | 4 | 4 | 4 | dBm | |
| | | $V_{CC} = 3.6 \text{ V}$ | 5 | 5 | 5 | dBm | |
| | f = 950 MHz | | | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 3 | 3 | 2 | dBm | |
| | | $V_{CC} = 3.3 \text{ V}$ | 4 | 4 | 3 | dBm | |
| | | $V_{CC} = 3.6 \text{ V}$ | 5 | 5 | 4 | dBm | |
| | | f = 2150 MHz | | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 2 | 1 | 0 | dBm | |
| | | $V_{CC} = 3.3 \text{ V}$ | 3 | 2 | 1 | dBm | |
| | | $V_{CC} = 3.6 \text{ V}$ | 4 | 3 | 1 | dBm | |

Table 12. Second-order intermodulation distance over temperature and supply voltages *Typical values*.

| Symbol | Parameter | Conditions | Tami | T _{amb} (°C) | | |
|--------|---------------------------------------|---|------|-----------------------|----|-----|
| | | | -40 | 25 | 85 | |
| ΔΙΜ2 | second-order intermodulation distance | $f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$ | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 48 | 48 | 42 | dBc |
| | | $V_{CC} = 3.3 \text{ V}$ | 52 | 45 | 41 | dBc |
| | | $V_{CC} = 3.6 \text{ V}$ | 49 | 44 | 41 | dBc |
| | | $f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$ | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 38 | 38 | 36 | dBc |
| | | $V_{CC} = 3.3 \text{ V}$ | 40 | 39 | 37 | dBc |
| | | $V_{CC} = 3.6 \text{ V}$ | 41 | 39 | 37 | dBc |

Table 13. Output third-order intercept point over temperature and supply voltages *Typical values*.

| Symbol | Parameter | Conditions | T _{amb} | T _{amb} (°C) | | |
|------------------|------------------------------------|---|------------------|-----------------------|----|------------|
| | | | -40 | 25 | 85 | |
| IP3 _O | output third-order intercept point | $f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$ | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 13 | 13 | 12 | dBm |
| | | $V_{CC} = 3.3 \text{ V}$ | 15 | 14 | 14 | dBm |
| | | $V_{CC} = 3.6 \text{ V}$ | 16 | 15 | 14 | dBm |
| | | $f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$ | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 13 | 12 | 12 | dBm |
| | | $V_{CC} = 3.3 \text{ V}$ | 15 | 14 | 13 | dBm |
| | | $V_{CC} = 3.6 \text{ V}$ | 16 | 15 | 14 | dBm dBm |
| | | $f_1 = 2150 \text{ MHz};$ $f_2 = 2151 \text{ MHz};$ $P_{drive} = -36 \text{ dBm}$ | | | | |
| | | $V_{CC} = 3.0 \text{ V}$ | 9 | 8 | 7 | dBm |
| | | $V_{CC} = 3.3 \text{ V}$ | 11 | 9 | 8 | dBm |
| | | $V_{CC} = 3.6 \text{ V}$ | 12 | 10 | 8 | dBm |

Table 14. -3 dB bandwidth over temperature and supply voltages *Typical values*.

| Symbol | Parameter | Conditions | T _{amb} (°C) | | | Unit |
|-------------------|-----------------|--------------------------|-----------------------|-------|-------|------|
| | | | -40 | 25 | 85 | |
| B _{-3dB} | -3 dB bandwidth | $V_{CC} = 3.0 \text{ V}$ | 2.875 | 2.832 | 2.745 | GHz |
| | | $V_{CC} = 3.3 \text{ V}$ | 2.902 | 2.849 | 2.763 | GHz |
| | | $V_{CC} = 3.6 \text{ V}$ | 2.920 | 2.866 | 2.775 | GHz |

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MMIC wideband amplifier

9. Test information

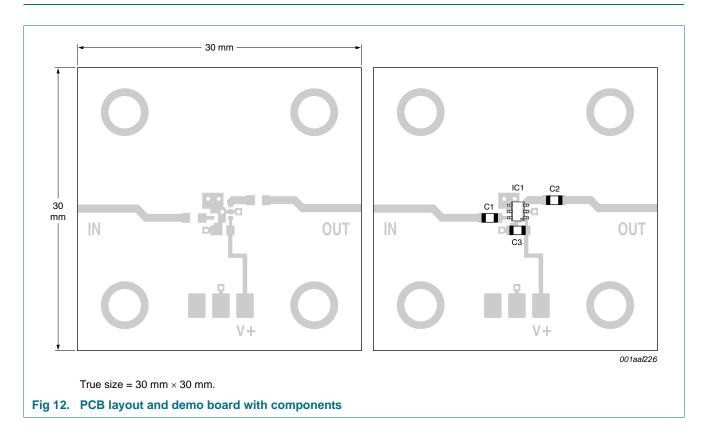


Table 15. List of components used for the typical application

| Component | Description | Value | Dimensions |
|-----------|-----------------------------------|--------|------------|
| C1, C2 | multilayer ceramic chip capacitor | 100 pF | 0603 |
| C3 | multilayer ceramic chip capacitor | 22 nF | 0603 |
| IC1 | BGA2801 MMIC | | SOT363 |

10. Package outline

Plastic surface-mounted package; 6 leads

SOT363

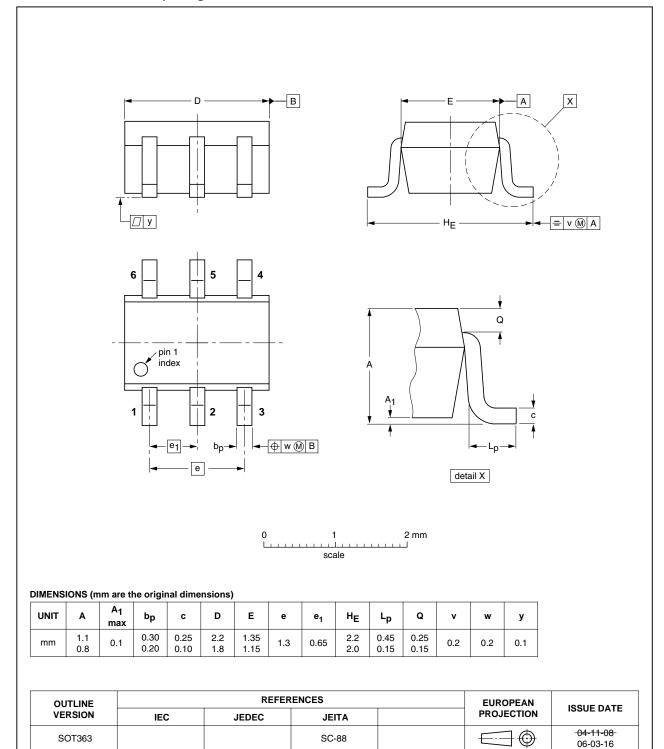


Fig 13. Package outline SOT363

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MMIC wideband amplifier

11. Abbreviations

Table 16. Abbreviations

| Acronym | Description |
|---------|---------------------------|
| DC | Direct Current |
| IF | Intermediate Frequency |
| LNA | Low-Noise Amplifier |
| LNB | Low-Noise Block converter |
| PCB | Printed-Circuit Board |
| RF | Radio Frequency |
| SMD | Surface Mounted Device |

12. Revision history

Table 17. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------|--------------|--------------------|---------------|------------|
| BGA2801 v.1 | 20100817 | Product data sheet | - | - |

N<u>牽彎器AA&AAII供</u>应商 BGA2801

MMIC wideband amplifier

13. Legal information

13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BGA2801

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BGA2801

MMIC wideband amplifier

15. Contents

| 1 | Product profile |
|------|---------------------------|
| 1.1 | General description |
| 1.2 | Features and benefits |
| 1.3 | Applications |
| 2 | Pinning information 1 |
| 3 | Ordering information 1 |
| 4 | Marking 2 |
| 5 | Limiting values |
| 6 | Thermal characteristics 2 |
| 7 | Characteristics 2 |
| 8 | Application information 3 |
| 8.1 | Application examples |
| 8.2 | Graphs |
| 8.3 | Tables |
| 9 | Test information |
| 10 | Package outline |
| 11 | Abbreviations |
| 12 | Revision history |
| 13 | Legal information |
| 13.1 | Data sheet status |
| 13.2 | Definitions |
| 13.3 | Disclaimers |
| 13.4 | Trademarks |
| 14 | Contact information 17 |
| 15 | Contents |

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